

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Applicant:	§	
Chien Chiang et al.	§	Art Unit: Unassigned
	§	
Serial No.: Unassigned	§	
	§	Examiner: Unassigned
Filed: July 1, 2003	§	
	§	
For: Method to Enhance Performance	§	Atty Docket: ITO.0536D1US
of Thermal Resistor Device	§	P8849D

Mail Stop Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**PRELIMINARY AMENDMENT**

Sir:

Please amend the above-referenced application.

**In the Specification**

Please insert at the first line --This is a divisional of prior Application No. 09/944,349, filed August 29, 2001, which is a continuation of prior Application No. 09/676,317, filed September 29, 2000, which issued on January 15, 2002 as U.S. Patent No. 6,339,544--.

**In the Claims**

Please cancel claims 1-22 and add new claims 23-25 before calculating the filing fee.

23 (New). A method comprising:

forming a dielectric material, a portion of which comprises a thermal conductivity less than silicon dioxide, between programmable material and a contact formed on a substrate, the dielectric material having an opening for the programmable material to couple to the contact.

24 (New). The method of claim 23, wherein forming the dielectric material comprises forming the portion which comprises the thermal conductivity less than silicon dioxide adjacent the programmable material.